

BIPOLAR ANALOG + DIGITAL INTEGRATED CIRCUIT

μ**ΡΒ1005Κ**

REFERENCE FREQUENCY 16.368 MHz, 2ND IF FREQUENCY 4.092 MHz RF/IF FREQUENCY DOWN-CONVERTER + PLL FREQUENCY SYNTHESIZER IC FOR GPS RECEIVER

DESCRIPTION

The μ PB1005K is a silicon monolithic integrated circuit for GPS receiver. This IC is designed as double conversion RF block integrated RF/IF down-converter + PLL frequency synthesizer on 1 chip.

The μ PB1005K features 36-pin plastic QFN, fixed prescaler and supply voltage. The 36-pin plastic QFN package is suitable for high density surface mounting. The fixed division internal prescaler is needless to input serial counter data. Supply voltage is 3 V. Thus, the μ PB1005K can make RF block fewer components and lower power consumption.

This IC is manufactured using NEC's 20 GHz f⊤ NESAT[™]III silicon bipolar process. This process uses direct silicon nitride passivation film and gold electrodes. These materials can protect the chip surface from pollution and prevent corrosion/migration. Thus, this IC realizes excellent performance, uniformity and reliability.

FEATURES

- Double conversion : fREFin = 16.368 MHz, f2ndiFout = 4.092 MHz
- Integrated RF block
 : RF/IF frequency down-converter + PLL frequency synthesizer
- High-density surface mountable : 36-pin plastic QFN ($6.0 \times 6.0 \times 0.95$ mm)
- Needless to input counter data : fixed division internal prescaler
- VCO side division : ÷ 200 (÷ 25, ÷ 8 serial prescaler)
 - Reference division : ÷ 2
- Supply voltage : Vcc = 2.7 to 3.3 V
- Low current consumption : Icc = 45.0 mA TYP.@Vcc = 3.0 V
- Gain adjustable externally : Gain control voltage pin (control voltage up vs. gain down)

APPLICATION

• Consumer use GPS receiver of reference frequency 16.368 MHz, 2nd IF frequency 4.092 MHz

ORDERING INFORMATION

Part Number	Package	Supplying Form
μΡΒ1005Κ-Ε1	36-pin plastic QFN	Embossed tape 12 mm wide. Pin 1 is in pull-out direction. Qty 2.5 kp/reel.

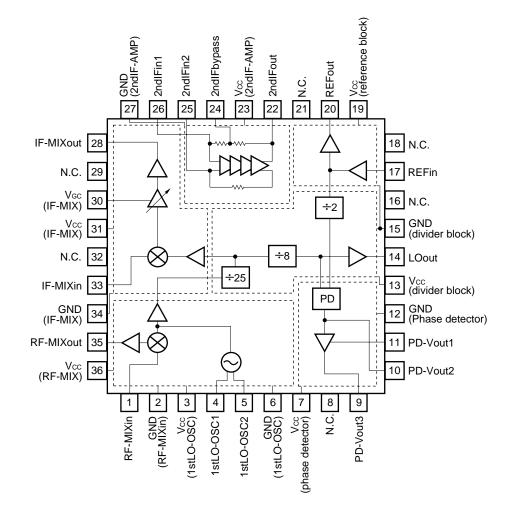
Remark To order evaluation samples, please contact your local NEC sales office. (Part number for sample order: μPB1005K)

Caution Electro-static sensitive device

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PIN CONNECTION AND INTERNAL BLOCK DIAGRAM

NEC



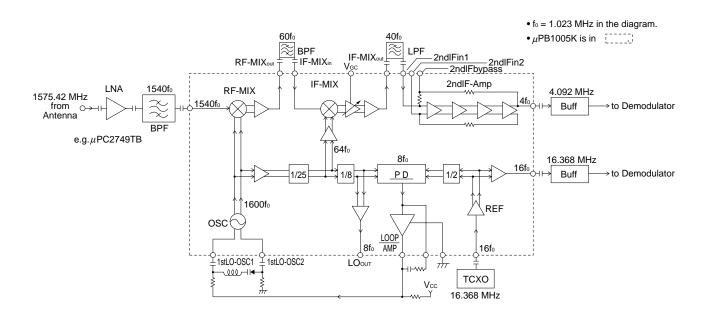
Туре	Part Number	Functions (Frequency unit: MHz)	Vcc (V)	Icc (mA)	CG (dB)	Package	Status
General	μPC2756T	RF down-converter with osc. Tr	2.7 to 3.3	6.0	14	6-pin minimold	Available
Purpose Wideband	μPC2756TB					6-pin super minimold	
Separate IC	μPC2753GR	IF down-converter with gain control amplifier	2.7 to 3.3	6.5	60 to 79	20-pin plastic SSOP (225 mil)	
Clock Frequency Specific 1 chip IC	μΡΒ1003GS	RF/IF down-converter + PLL synthesizer REF = 18.414 1stIF = 28.644/2ndIF = 1.023	2.7 to 3.3	37.5	72 to 92	30-pin plastic SSOP (300 mil)	Discontinued
	μPB1004GS	RF/IF down-converter	2.7 to 3.3	37.5	72 to 92		
	μPB1005GS	+ PLL synthesizer REF = 16.368	2.7 to 3.3	45.0	72 to 92		Available
	μΡΒ1005K	1stIF = 61.380/2ndIF = 4.092				36-pin plastic QFN	

PRODUCT LINE-UP (TA = +25 °C, Vcc = 3.0 V)

Notice Typical performance. Please refer to ELECTRICAL CHARACTERISTICS in detail. To know the associated products, please refer to their latest data sheets.

SYSTEM APPLICATION EXAMPLE

GPS receiver RF block diagram



Caution This diagram schematically shows only the μ PB1005K's internal functions on the system. This diagram does not present the actual application circuits.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Conditions	Rating	Unit
Supply Voltage	Vcc	T _A = +25 °C	3.6	V
Total Circuit Current	lcc	T _A = +25 °C	120	mA
Power Dissipation	PD	Mounted on double-sided copper clad $50 \times 50 \times 1.6$ mm epoxy glass PWB (T _A = +85 °C)	430	mW
Operating Ambient Temperature	TA		-40 to +85	°C
Storage Temperature	Tstg		-55 to +150	°C

RECOMMENDED OPERATING RANGE

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	Vcc	2.7	3.0	3.3	V
Operating Ambient Temperature	TA	-40	+25	+85	°C
RF Input Frequency	f RFin	_	1575.42	_	MHz
1st LO Oscillating Frequency	f1stLOin	1616.80	1636.80	1656.80	MHz
1st IF Input Frequency	f 1stlFin	—	61.38	_	MHz
2nd LO Input Frequency	f2ndLOin	—	65.472	_	MHz
2nd IF Input/output Frequency	f2ndlFin f2ndlFout	—	4.092	_	MHz
Reference Input/output Frequency	freFin freFout	_	16.368	_	MHz
LO Output Frequency	f LOout	—	8.184	_	MHz

ELECTRICAL CHARACTERISTICS (Unless otherwise specified T_A = +25 °C, Vcc = 3.0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Total Circuit Current	lcctotal	lcc1 + lcc2 + lcc3 + lcc4	32.0	45.0	60.0	mA
		/Hz, f1stL0in = 1636.80 MHz, PL0in = -10 dB			0010	
Circuit Current 1	6.0	10.0	14.0	mA		
RF Conversion Gain	CGRF	No Signals P _{RFin} = -40 dBm	12.5	15.5	18.5	dB
RF-SSB Noise Figure	NFRF	$P_{\text{RFin}} = -40 \text{ dBm}$	7.0	10.0	13.0	dB
Maximum IF Output	P _{O(sat)} RF	P _{RFin} = -10 dBm	-5.5	-2.5	+0.5	dBm
· ·	In = 61.38 MH	I z, f _{2ndLOIn} = 65.472 MHz, Zs = 50 Ω , ZL = 2	: kΩ)			
Circuit Current 2	Icc2	No Signals	3.4	5.3	7.2	mA
IF Conversion Voltage Gain	CG(GV)IF	at Maximum Gain, P1stlFin = -50 dBm	38	41	44	dB
IF-SSB Noise Figure	NFIF	at Maximum Gain, P₁stlFin = −50 dBm	8.5	11.5	14.5	dB
Maximum 2ndIF Output	Po(sat)IF	at Maximum Gain, P₁stlFin = −20 dBm	-9.5	-6.5	-3.5	dBm
Gain Control Voltage	Vgc	Voltage at Maximum Gain CG⊫	_	_	1.0	V
Gain Control Range	Dgc	P1stlFin = -50 dBm	20	_	_	dB
2nd IF Amplifier (f2ndIF = 4.092	MHz, Zs = 50) Ω, ZL = 2 kΩ)				
Circuit Current 3	Icc3	No Signals	1.55	2.40	3.25	mA
Voltage Gain	Gv	P _{2ndlFin} = -60 dBm	37	40	43	dB
Output Power	P2ndIFout	P _{2ndlFin} = -30 dBm	-14.5	-11.5	-8.5	dBm
PLL Synthesizer Block						
Circuit Current 4	Icc4	PLL All Block Operating	18.5	28.5	38.5	mA
Phase Comparing Frequency	fpd	PLL Loop	8.0	8.184	8.4	MHz
Reference Input Minimum Level	VREFin	$Z_{L} = 10 \text{ k}\Omega//20 \text{ pF}^{\text{Note}}$	200			mV _{P-P}
Loop Filter Output Level (H)	VLP(H)		2.8			V
Loop Filter Output Level (L)	VLP(L)				0.4	V
Reference Output Swing	VREFout	$Z_L = 10 \text{ k}\Omega//2 \text{ pF}^{\text{Note}}$	1.0			Vp-p

Note Impedance of measurement equipment

STANDARD CHARACTERISTICS (Unless otherwise specified T_A = +25 °C, Vcc = 3.0 V)

Parameter	Symbol	Conditions	Reference	Unit	
RF Down-converter Block (P1s	tLOin = -10 dBr	n, Zs = ZL = 50 Ω)			
LO Leakage to IF Pin	LOif	f _{1stLOin} = 1 636.80 MHz	-30	dBm	
LO Leakage to RF Pin	LOrf	f _{1stLOin} = 1 636.80 MHz	-30	dBm	
Input 3rd Order Intercept Point	IIP₃RF	$f_{RFin}1 = 1\ 600\ MHz,\ f_{RFin}2 = 1605\ MHz$ $f_{1stLOin} = 1\ 660\ MHz$	-13	dBm	
IF Down-converter Block (1st	LO oscillating,	$Zs = 50 \Omega$, $ZL = 2 k\Omega$)			
LO Leakage to 2nd IF	LO _{2ndif}	f _{2ndLOin} = 65.472 MHz	-20	dBm	
LO Leakage to 1st IF	LO _{1stif}	f2ndL0in = 65.472 MHz	-40	dBm	
Input 3rd Order Intercept Point	llP₃lF	f1stlFin1 = 61.38 MHz, f1stlFin2 = 61.48 MHz f2ndLOin = 65.472 MHz	-34	dBm	
VCO Block					
Phase Noise	C/N	PLL Loop, Δ 1kHz of VCO wave	-78	dBc/Hz	

PIN EXPLANATION

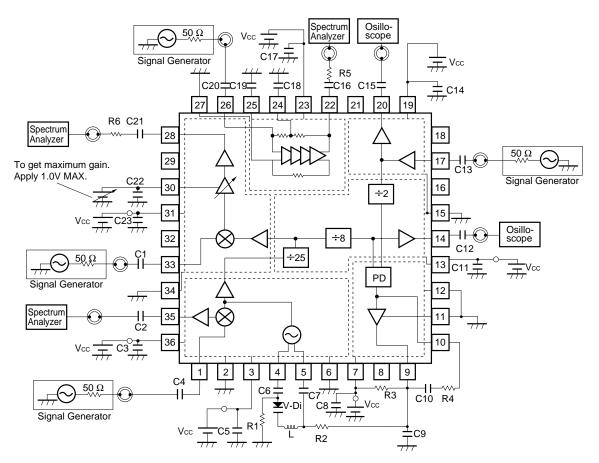
Pin No.	Pin Name	Applied Voltage (V)	Pin Voltage (V)	Function and Application	Internal Equivalent Circuit
35	RX-MIXout		1.68	Output pin of RF mixer. 1st IF filter must be inserted between pin 33 & 35.	36 •••
36	Vcc (RF-MIX)	2.7 to 3.3		Supply voltage pin of RF mixer block. This pin must be decoupled with capacitor (example: 1 000 pF).	
1	RF-MIXin	_	1.20	Input pin of RF mixer. 1 575.42 MHz band pass filter can be inserted between pin 1 and external LNA.	
2	GND (RF-MIX)	0	—	Ground pin RF mixer.	
3	V _{cc} (1stLO-OSC)	2.7 to 3.3	_	Supply voltage pin of differential amplifier for 1st LO oscillator circuit.	(3) Vcc
4	1stLO-OSC1	—	1.88	Pin 4 & 5 are each base pin of differential amplifier for 1st LO oscillator. These pins should be	RF-MIX or Prescaler input
5	1stLO-OSC2	_	1.88	equipped with LC and varactor to oscillate on 1 636.80 MHz as VCO.	
6	GND (1stLO-OSC)	0	_	Ground pin of differential amplifier for 1st LO oscillator circuit.	
7	Vcc (phase detector)	2.7 to 3.3	_	Supply voltage pin of phase detector and active loop filter.	
8	N.C.	—	_	Non connection	
9	PD-Vout3	Pull-up with resistor	_	Pins of active loop filter for tuning voltage output. The active transistors	
10	PD-Vout2		Output in accordance with phase difference	configured with darlington pair are built on chip. Pin 11 should be pulled down with external resistor. Pin 9 to 10 should be	
11	PD-Vout1	Pull-up with resistor	_	equipped with external RC in order to adjust dumping factor and cutoff frequency. This tuning voltage output must be connected to varactor diode of 1st LO-OSC.	
12	GND (phase detector)	0		Ground pin of phase detector + active loop filter.	

Pin No.	Pin Name	Applied Voltage (V)	Pin Voltage (V)	Function and Application	Internal Equivalent Circuit
13	Vcc (divider block)	2.7 to 3.3	_	Supply voltage pin of prescalers.	
14	LOout	_	2.08	Monitor pin of comparison frequency at phase detector.	1st + 25 + 8 + 10 + 14 + 2 + 10 + 12 + 10 + 12 + 10 + 12 + 10 + 12 + 10 + 12 + 10 + 12 + 10 + 12 + 12
15	GND (divider block)	0	_	Ground pin of prescalers + LOout amplifier	
16	N.C.	—	—	Non connection	
17	REFin		1.96	Input pin of reference frequency. This pin should be equipped with external 16.368 MHz oscillator (example: TCXO).	
18	N.C.	_		Non connection	
19	Vcc (reference block)	2.7 to 3.3		Supply voltage pin of input/output amplifiers in reference block.	
20	REFout		1.65	Output pin of reference frequency. The frequency from pin 17 can be took out as 1 V _{P-P} swing.	
21	N.C.	_	_	Non connection	
22	2ndlFout		1.56	Output pin of 2nd IF amplifier. This pin output 4.092 MHz clipped sinewave. This pin should be equipped with external inverter to adjust level to next stage on user's system.	
23	Vcc (2ndIF-AMP)	2.7 to 3.3	_	Supply voltage pin of 2nd IF amplifier.	
24	2ndIF bypass	_	2.30	Bypass pin of 2nd IF amplifier input 1. This pin should be grounded through capacitor.	
25	2ndlFin2		2.35	Pin of 2nd IF amplifier input 2. This pin should be grounded through capacitor.	
26	2ndlFin1	—	2.35	Pin of 2nd IF amplifier input 1. 2nd IF filter can be inserted between pin 26 & 28.	
27	GND (2ndIF-AMP)	0		Ground pin of 2nd IF amplifier.	

Pin No.	Pin Name	Applied Voltage (V)	Pin Voltage (V)	Function and Application	Internal Equivalent Circuit
28	IF-MIXout		1.15	Output pin from IF mixer. IF mixer output signal goes through gain control amplifier before this emitter follower output port.	
29	N.C.	_	_	Non connection	
30	Vec (IF-MIX)	0 to 3.3		Gain control voltage pin of IF mixer output amplifier. This voltage performs forward control (V _{Gc} up \rightarrow Gain down).	33 2nd LO 34
31	Vcc (IF-MIX)	2.7 to 3.3		Supply voltage pin of IF mixer, gain control amplifier and emitter follower transistor.	
32	N.C.	_		Non connection	
33	IF-MIXin		2.00	Input pin of IF mixer.	
34	GND (IF-MIX)	0	_	Ground pin of IF mixer.	

Caution Ground pattern on the board must be formed as wide as possible to minimize ground impedance.

TEST CIRCUIT



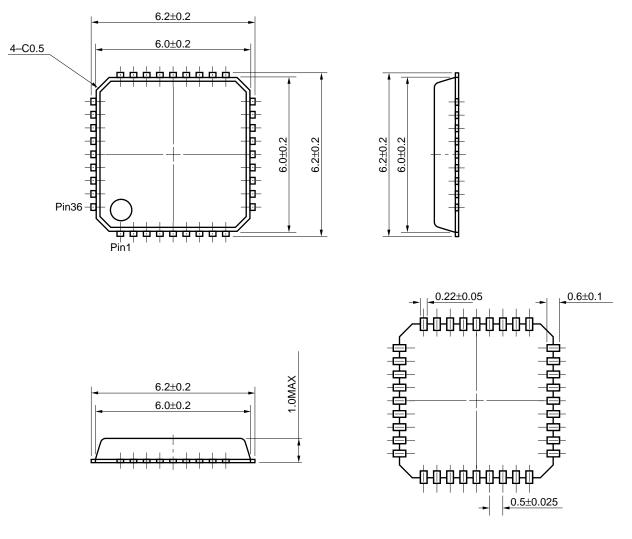
Spectrum Analyzer : measure frequency Oscilloscope : measure output voltage swing

Component List

Form	Symbol	Value
Chip capacitor	C1 to C5, C8, C11 to C15, C17, C18, C22	1 000 pF
	C6, C7	24 pF (UJ)
	C9	1800 pF
	C10	33 nF
	C19	10 000 pF
	C23	1 <i>µ</i> F
	C16, C20	0.1 <i>μ</i> F
	C21	0.01 μF
Chip resistor	R1, R2	4.7 kΩ
	R3	6.2 kΩ
	R4	1.2 kΩ
	R5, R6	1.95 kΩ
Varactor Diode	V-Di	1SV285
Chip Inductor	L	3.9 nH

PACKAGE DIMENSIONS

36 PIN PLASTIC QFN (UNIT: mm)



Bottom View

NOTE ON CORRECT USE

- (1) Observe precautions for handling because of electro-static sensitive devices.
- (2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent abnormal oscillation).
- (3) Keep the track length of the ground pins as short as possible.
- (4) Connect a bypass capacitor (example: 1 000 pF) to the Vcc pin.
- (5) Frequency signal input/output pins must be each coupled with external capacitor for DC cut.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your NEC sales representative.

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared Reflow	Package peak temperature: 235 °C or below Time: 30 seconds or less (at 210 °C) Count: 2, Exposure limit ^{Note} : None	IR35-00-2
Partial Heating	Pin temperature: 300 ° C Time: 3 seconds or less (per side of device) Exposure limit ^{Note} : None	_

Note After opening the dry pack, keep it in a place below 25 °C and 65 % RH for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

For details of recommended soldering conditions for surface mounting, refer to information document **SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL (C10535E).**

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